

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)



ON Semiconductor®

<http://onsemi.com>

Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain – Bandwidth Product
- Compact TO–220 Package
- These Devices are Pb–Free and are RoHS Compliant*

**3 AMPERE
POWER TRANSISTORS
COMPLEMENTARY SILICON
40–60–80–100 VOLTS,
40 WATTS**

MAXIMUM RATINGS

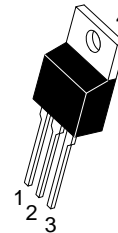
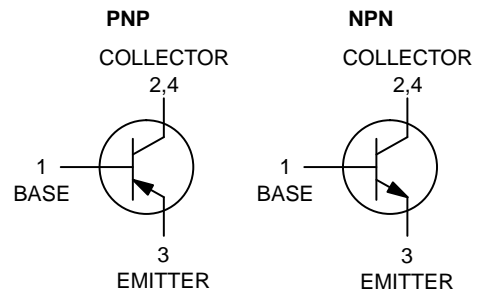
Rating	Symbol	Value	Unit
Collector – Emitter Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V_{CEO}	40 60 80 100	Vdc
Collector–Base Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V_{CB}	40 60 80 100	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous	I_C	3.0	Adc
Collector Current – Peak	I_{CM}	5.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	W W/ $^\circ\text{C}$
Unclamped Inductive Load Energy (Note 1)	E	32	mJ
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $I_C = 1.8\text{ A}$, $L = 20\text{ mH}$, P.R.F. = 10 Hz, $V_{CC} = 10\text{ V}$, $R_{BE} = 100\ \Omega$

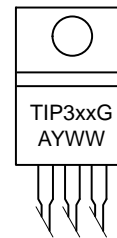
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	3.125	$^\circ\text{C/W}$



TO-220
CASE 221A
STYLE 1

MARKING DIAGRAM



TIP3xx = Device Code
xx = 1, 1A, 1B, 1C,
2, 2A, 2B, 2C,
A = Assembly Location
Y = Year
WW = Work Week
G = Pb–Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 2) ($I_C = 30\text{ mAdc}$, $I_B = 0$) TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	$V_{CE(sus)}$	40 60 80 100	– – – –	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) TIP31G, TIP32G, TIP31AG, TIP32AG ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$) TIP31BG, TIP31CG, TIP32BG, TIP32CG	I_{CEO}	– –	0.3 0.3	mAdc
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $V_{EB} = 0$) TIP31G, TIP32G ($V_{CE} = 60\text{ Vdc}$, $V_{EB} = 0$) TIP31AG, TIP32AG ($V_{CE} = 80\text{ Vdc}$, $V_{EB} = 0$) TIP31BG, TIP32BG ($V_{CE} = 100\text{ Vdc}$, $V_{EB} = 0$) TIP31CG, TIP32CG	I_{CES}	– – – –	200 200 200 200	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	1.0	mAdc
ON CHARACTERISTICS (Note 2)				
DC Current Gain ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	25 10	– 50	–
Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ Adc}$, $I_B = 375\text{ mAdc}$)	$V_{CE(sat)}$	–	1.2	Vdc
Base–Emitter On Voltage ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	3.0	–	MHz
Small–Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	20	–	–

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

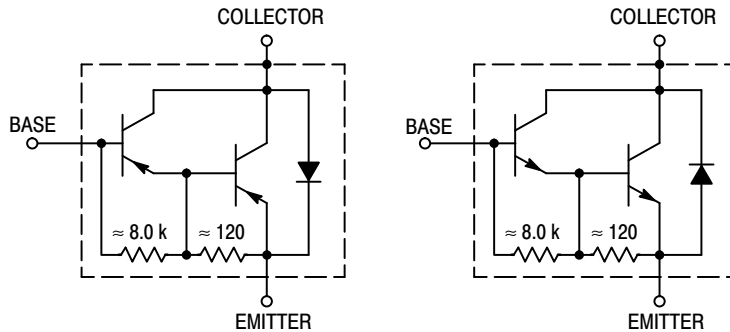


Figure 1. Darlington Circuit Schematic

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

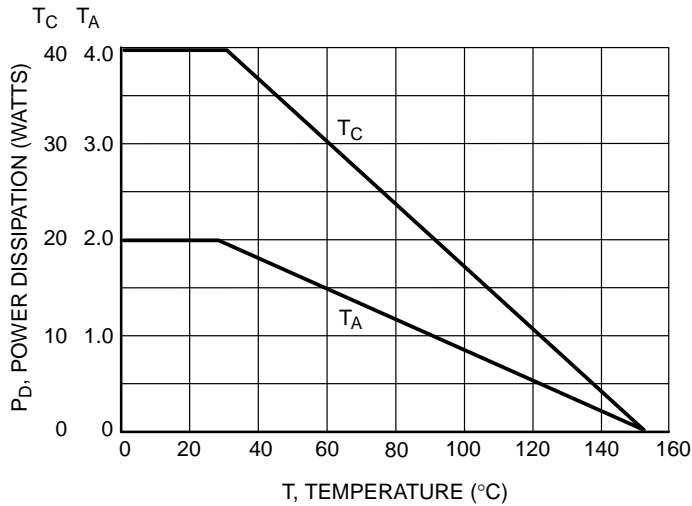
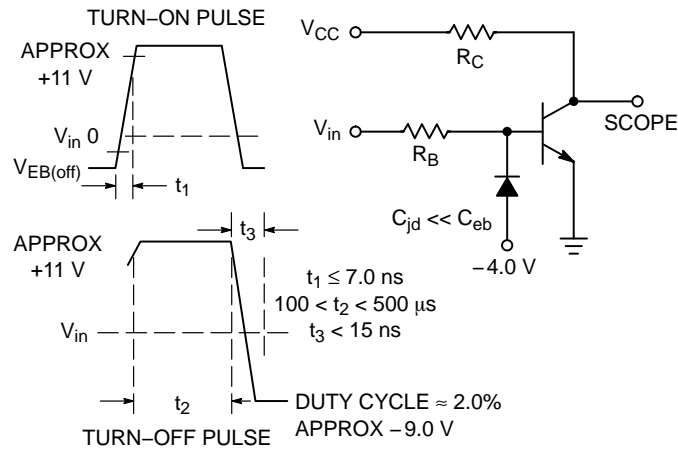


Figure 2. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 3. Switching Time Equivalent Circuit

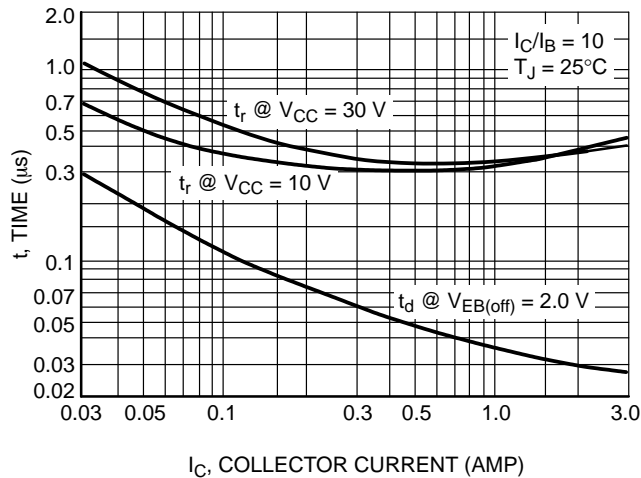


Figure 4. Turn-On Time

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

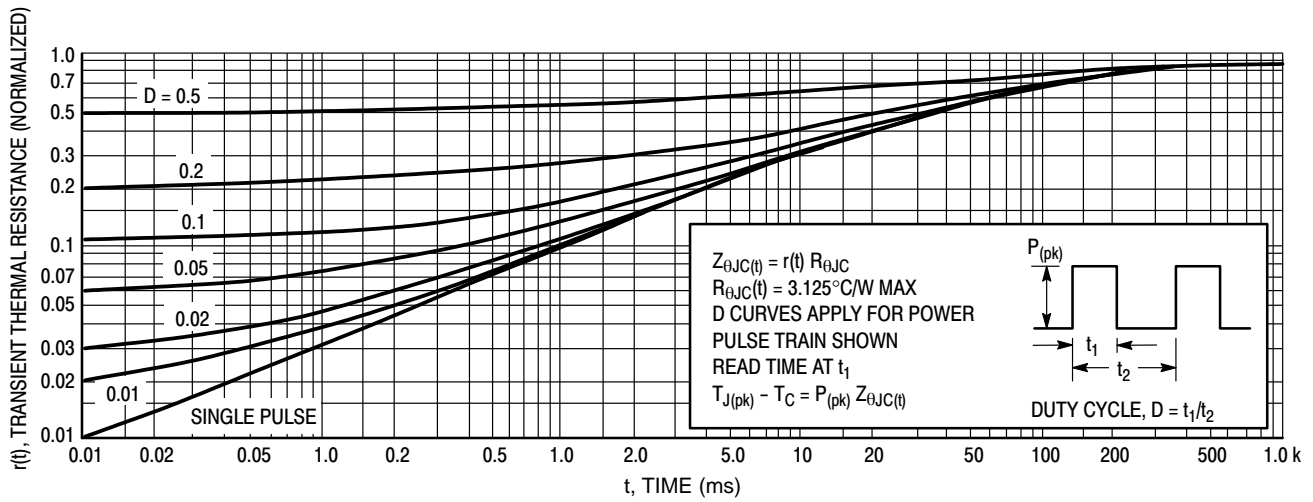


Figure 5. Thermal Response

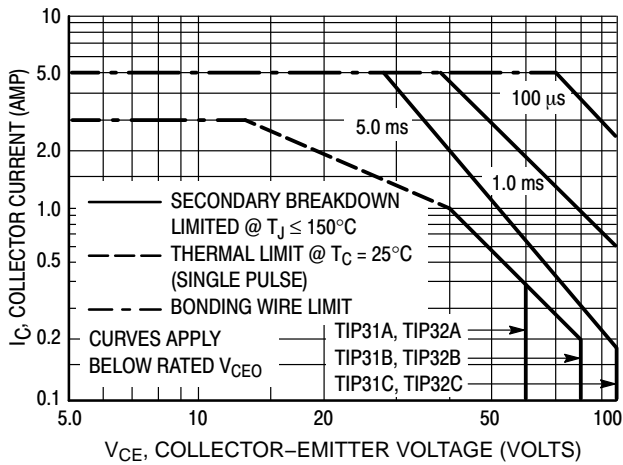


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

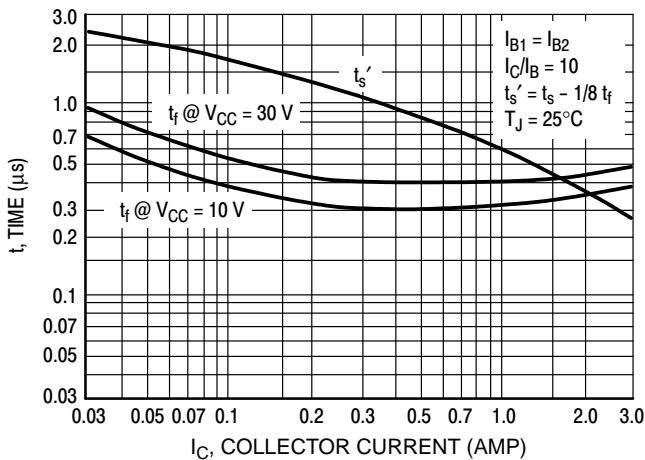


Figure 7. Turn-Off Time

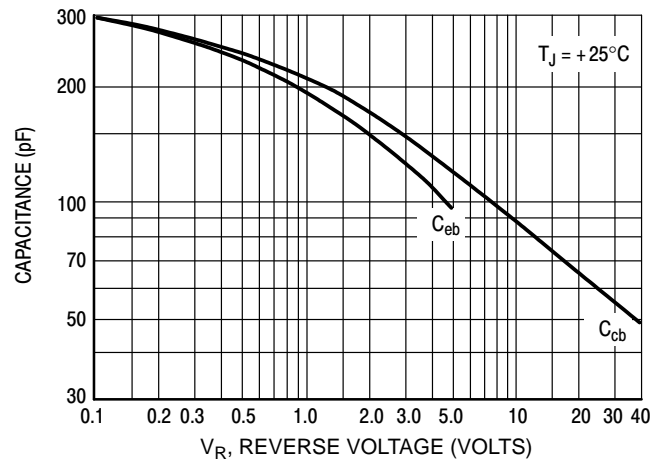


Figure 8. Capacitance

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

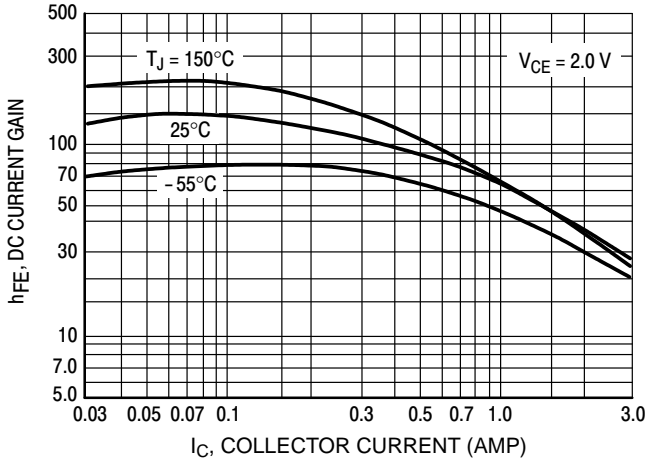


Figure 9. DC Current Gain

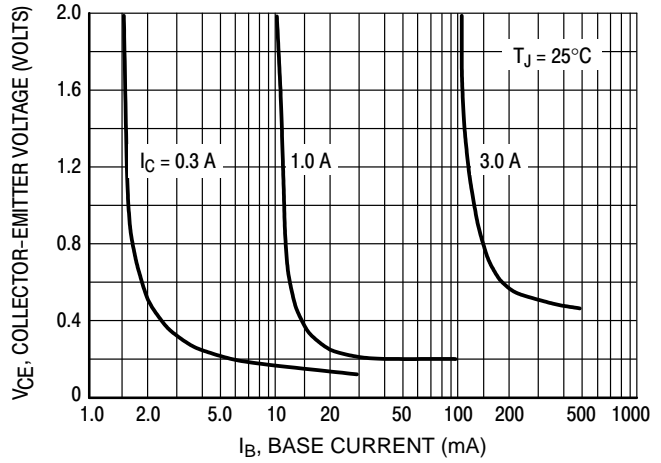


Figure 10. Collector Saturation Region

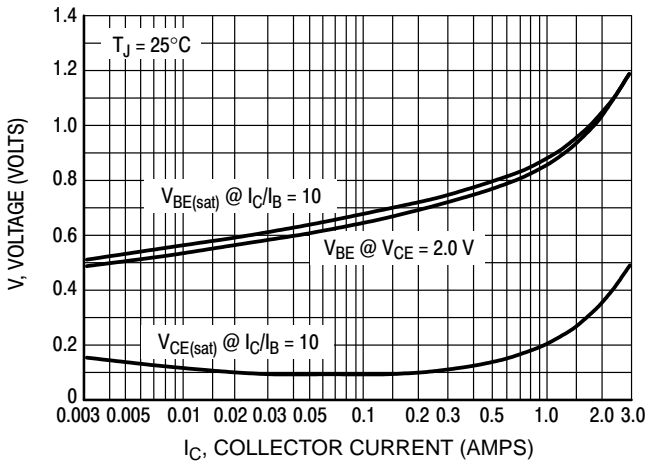


Figure 11. "On" Voltages

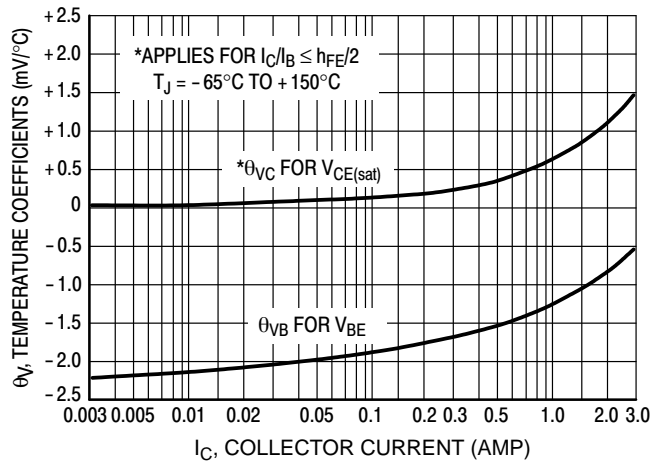


Figure 12. Temperature Coefficients

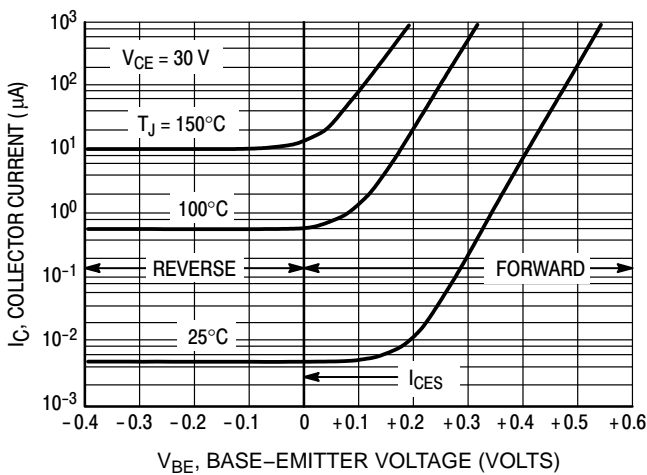


Figure 13. Collector Cut-Off Region

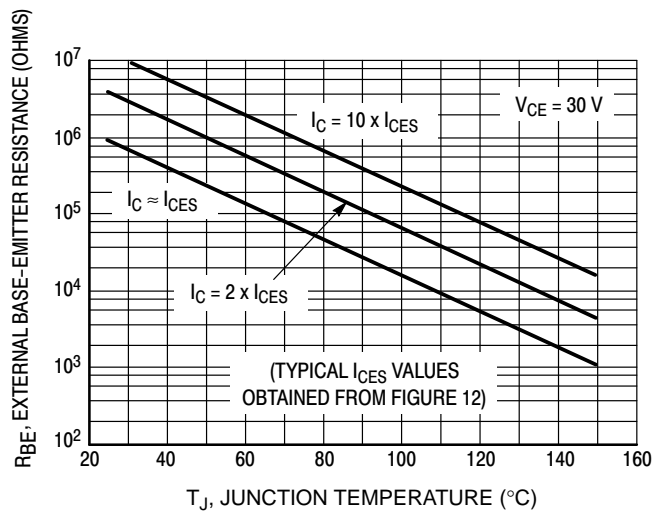


Figure 14. Effects of Base-Emitter Resistance

**TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG,
TIP32CG (PNP)**

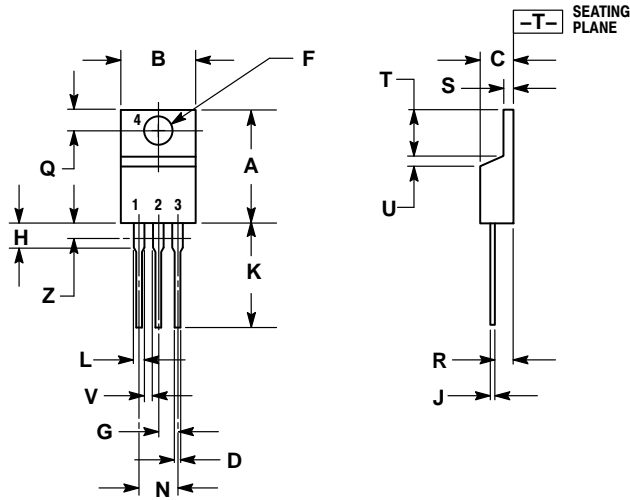
ORDERING INFORMATION

Device	Package	Shipping
TIP31G	TO-220 (Pb-Free)	50 Units / Rail
TIP31AG	TO-220 (Pb-Free)	50 Units / Rail
TIP31BG	TO-220 (Pb-Free)	50 Units / Rail
TIP31CG	TO-220 (Pb-Free)	50 Units / Rail
TIP32G	TO-220 (Pb-Free)	50 Units / Rail
TIP32AG	TO-220 (Pb-Free)	50 Units / Rail
TIP32BG	TO-220 (Pb-Free)	50 Units / Rail
TIP32CG	TO-220 (Pb-Free)	50 Units / Rail

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AG




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1: BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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